

MUN2135, MMUN2135L, MUN5135, DTA123JE, DTA123JM3, NSBA123JF3



Digital Transistors (BRT) $R1 = 2.2 \text{ k}\Omega$, $R2 = 47 \text{ k}\Omega$

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

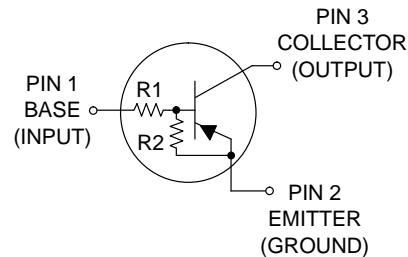
Rating	Symbol	Max	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current – Continuous	I_C	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	12	Vdc
Input Reverse Voltage	$V_{IN(rev)}$	5	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

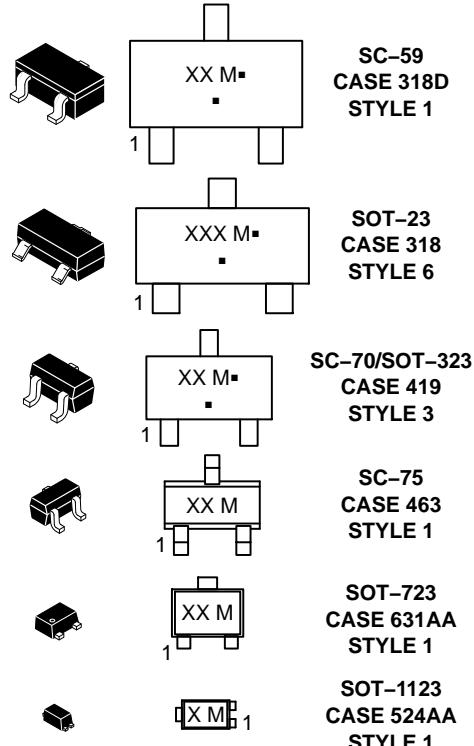
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PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

MUN2135, MMUN2135L, MUN5135, DTA123JE, DTA123JM3, NSBA123JF3

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
MUN2135T1G	6R	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2135LT1G, NSVMMUN2135LT1G*	ACA	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5135T1G	6M	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA123JET1G	6M	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA123JM3T5G, NSVDTA123JM3T5G*	6M	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA123JF3T5G	J (90°)**	SOT-1123 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

**(XX°) = Degree rotation in the clockwise direction.

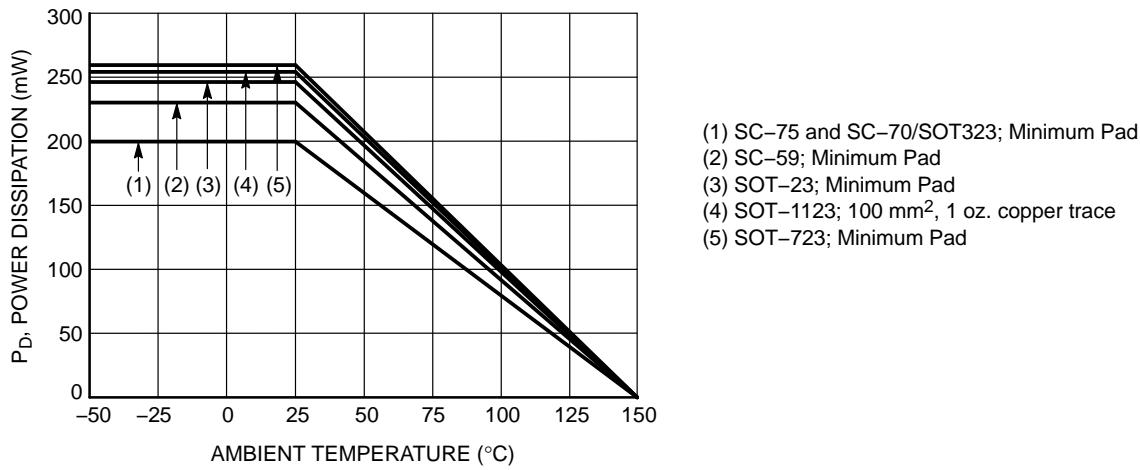


Figure 1. Derating Curve

MUN2135, MMUN2135L, MUN5135, DTA123JE, DTA123JM3, NSBA123JF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2135)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	230 338 1.8 2.7	mW mW/ $^\circ\text{C}$
Derate above 25°C		(Note 1) (Note 2) (Note 1) (Note 2)	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	540 370	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	264 287	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SOT-23) (MMUN2135L)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	246 400 2.0 3.2	mW mW/ $^\circ\text{C}$
Derate above 25°C		(Note 1) (Note 2) (Note 1) (Note 2)	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	508 311	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	174 208	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5135)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	202 310 1.6 2.5	mW mW/ $^\circ\text{C}$
Derate above 25°C		(Note 1) (Note 2) (Note 1) (Note 2)	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	618 403	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	280 332	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SC-75) (DTA123JE)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	200 300 1.6 2.4	mW mW/ $^\circ\text{C}$
Derate above 25°C		(Note 1) (Note 2) (Note 1) (Note 2)	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	600 400	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SOT-723) (DTA123JM3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	260 600 2.0 4.8	mW mW/ $^\circ\text{C}$
Derate above 25°C		(Note 1) (Note 2) (Note 1) (Note 2)	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	480 205	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm², 1 oz. copper traces, still air.
4. FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBA123JF3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	254 297 2.0 2.4	mW $\text{mW}/^\circ\text{C}$
Derate above 25°C			
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	493 421	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	193	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm², 1 oz. copper traces, still air.
4. FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$)	I_{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$)	I_{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$)	I_{EBO}	-	-	0.2	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) ($I_C = 2.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	50	-	-	Vdc

ON CHARACTERISTICS

DC Current Gain (Note 5) ($I_C = 5.0\text{ mA}$, $V_{CE} = 10\text{ V}$)	h_{FE}	80	140	-	
Collector – Emitter Saturation Voltage (Note 5) ($I_C = 10\text{ mA}$, $I_B = 0.3\text{ mA}$)	$V_{CE(\text{sat})}$	-	-	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0\text{ V}$, $I_C = 100\text{ }\mu\text{A}$)	$V_{i(\text{off})}$	-	0.6	0.5	Vdc
Input Voltage (on) ($V_{CE} = 0.3\text{ V}$, $I_C = 5.0\text{ mA}$)	$V_{i(\text{on})}$	1.1	0.8	-	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OL}	-	-	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	-	-	Vdc
Input Resistor	R_1	1.5	2.2	2.9	k Ω
Resistor Ratio	R_1/R_2	0.038	0.047	0.056	

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS
MUN2135, MMUN2135L, MUN5135, DTA123JE, DTA123JM3

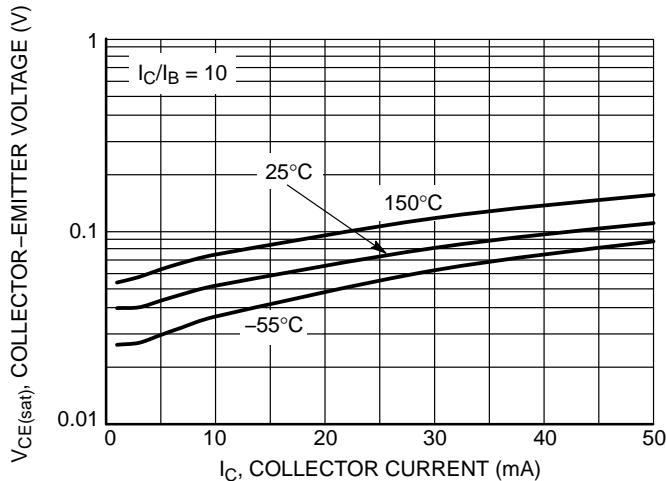


Figure 2. $V_{CE(sat)}$ vs. I_C

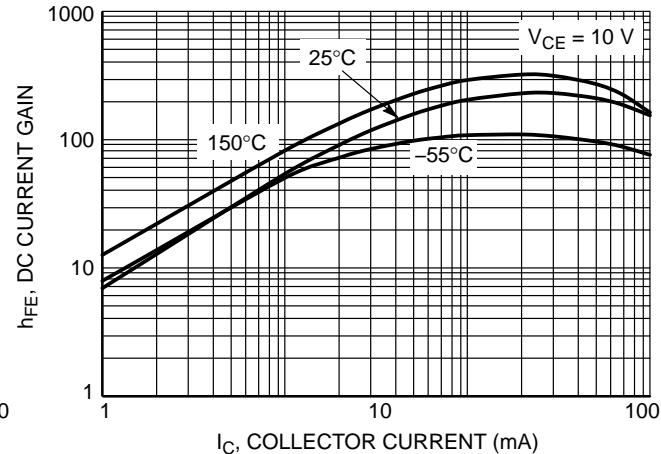


Figure 3. DC Current Gain

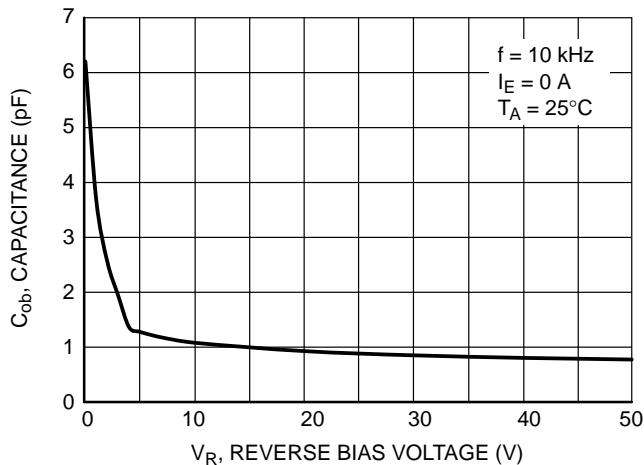


Figure 4. Output Capacitance

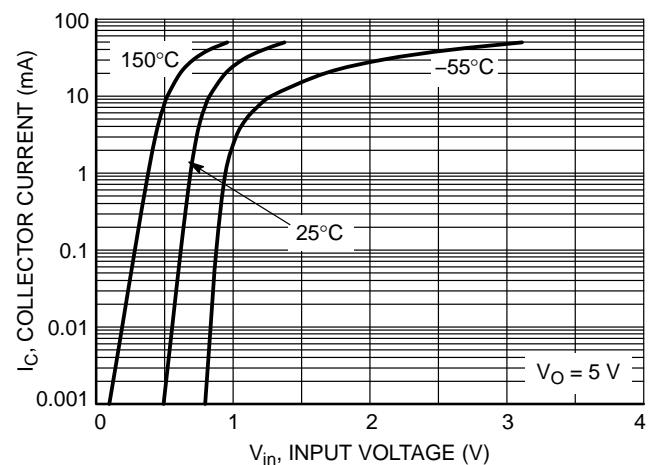


Figure 5. Output Current vs. Input Voltage

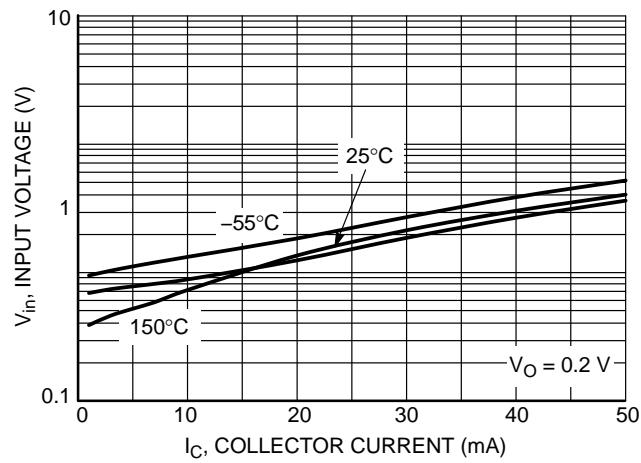
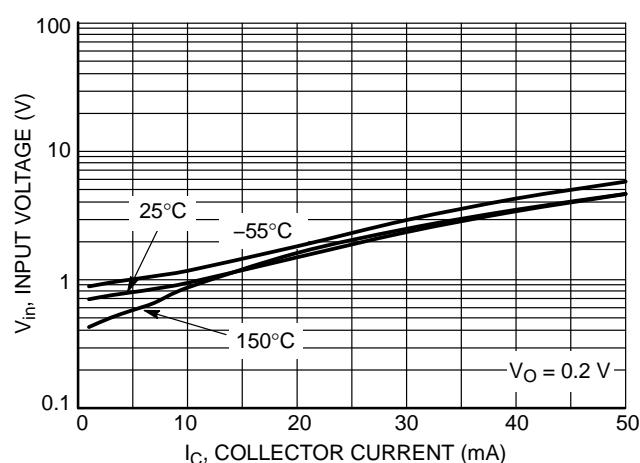
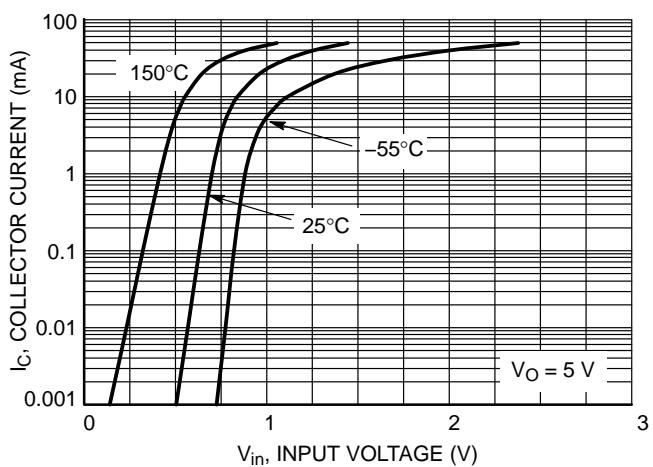
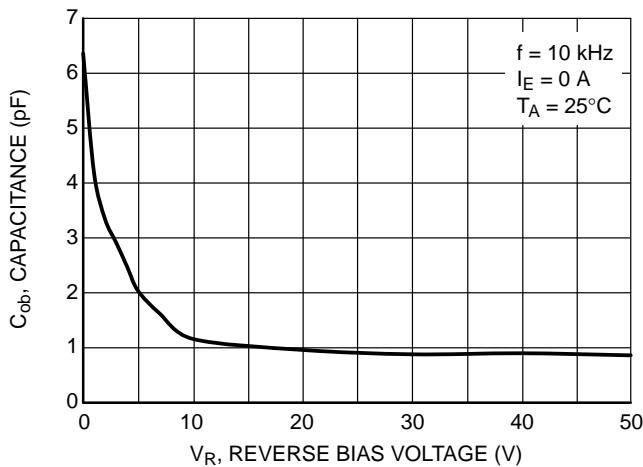
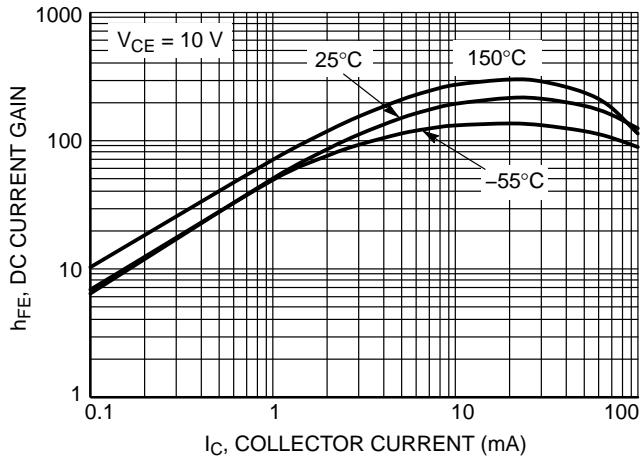
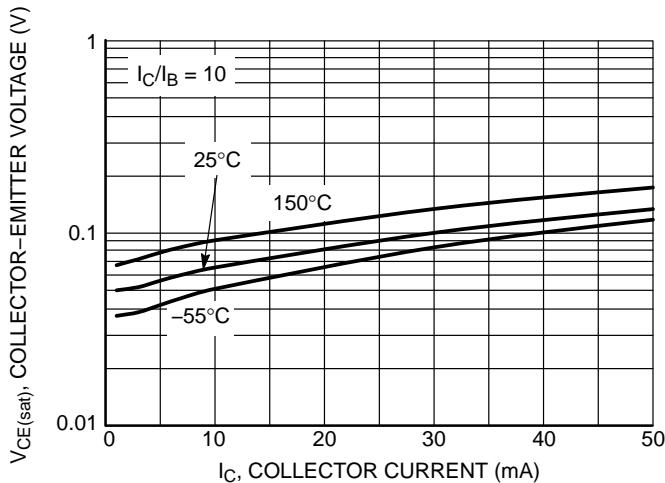


Figure 6. Input Voltage vs. Output Current

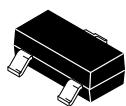
TYPICAL CHARACTERISTICS
NSBA123JF3



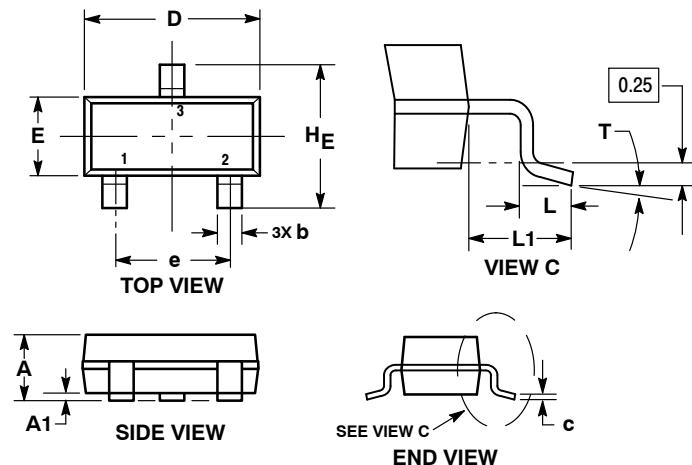
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 4:1



SOT-23 (TO-236) CASE 318-08 ISSUE AS

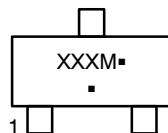
DATE 30 JAN 2018

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H _E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

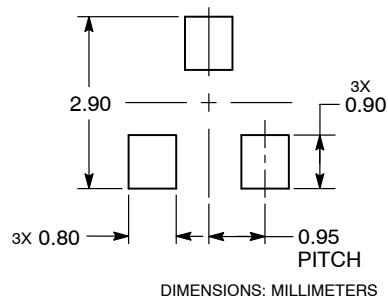
GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "■", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT



STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. Emitter
3. Collector

STYLE 7:
PIN 1. Emitter
2. Base
3. Collector

STYLE 8:
PIN 1. Anode
2. No Connection
3. Cathode

STYLE 9:
PIN 1. Anode
2. Anode
3. Cathode

STYLE 10:
PIN 1. Drain
2. Source
3. Gate

STYLE 11:
PIN 1. Anode
2. Cathode
3. Cathode-Anode

STYLE 12:
PIN 1. Cathode
2. Cathode
3. Anode

STYLE 13:
PIN 1. Source
2. Drain
3. Gate

STYLE 14:
PIN 1. Cathode
2. Gate
3. Anode

STYLE 15:
PIN 1. Gate
2. Cathode
3. Anode

STYLE 16:
PIN 1. Anode
2. Cathode
3. Cathode

STYLE 17:
PIN 1. No Connection
2. Anode
3. Cathode

STYLE 18:
PIN 1. No Connection
2. Cathode
3. Anode

STYLE 19:
PIN 1. Cathode
2. Anode
3. Cathode-Anode

STYLE 20:
PIN 1. Cathode
2. Anode
3. Gate

STYLE 21:
PIN 1. Gate
2. Source
3. Drain

STYLE 22:
PIN 1. Return
2. Output
3. Input

STYLE 23:
PIN 1. Anode
2. Anode
3. Cathode

STYLE 24:
PIN 1. Gate
2. Drain
3. Source

STYLE 25:
PIN 1. Anode
2. Cathode
3. Gate

STYLE 26:
PIN 1. Cathode
2. Anode
3. No Connection

STYLE 27:
PIN 1. Cathode
2. Cathode
3. Cathode

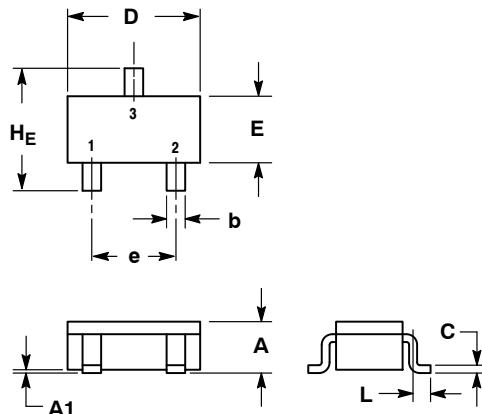
STYLE 28:
PIN 1. Anode
2. Anode
3. Anode

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DESCRIPTION:	SOT-23 (TO-236)	PAGE 1 OF 1

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SCALE 2:1



SC-59
CASE 318D-04
ISSUE H

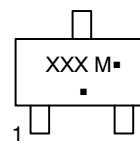
DATE 28 JUN 2012

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.80	3.00	0.099	0.110	0.118

**GENERIC
MARKING DIAGRAM**

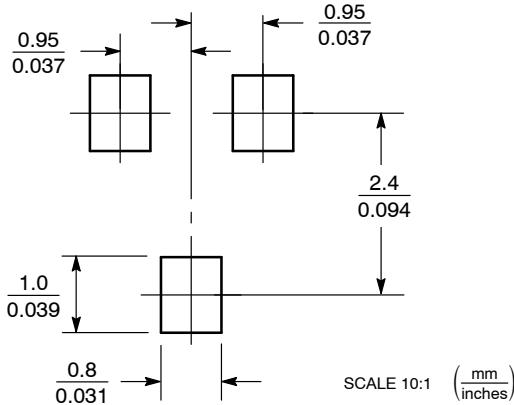


XXX = Specific Device Code
M = Date Code
■ = Pb-Free Package*

(*Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

SOLDERING FOOTPRINT*



SCALE 10:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:
PIN 1. BASE
2. Emitter
3. Collector

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. N.C.
3. ANODE

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE

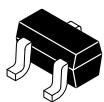
STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE/CATHODE

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DESCRIPTION:	SC-59	PAGE 1 OF 1

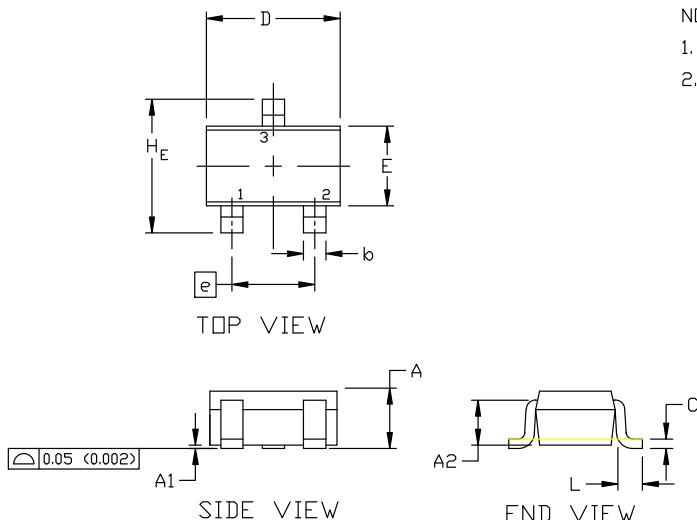
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MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

onsemiTM



SCALE 4:1



SC-70 (SOT-323)
CASE 419
ISSUE R

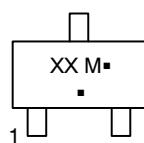
DATE 11 OCT 2022

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

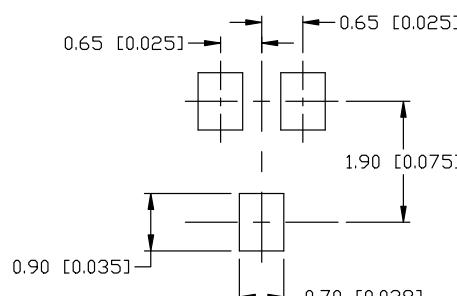
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

**GENERIC
MARKING DIAGRAM**



XX = Specific Device Code
M = Date Code
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the [ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D](#).

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. Emitter 3. Collector	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE
STYLE 6: PIN 1. Emitter 2. BASE 3. COLLECTOR	STYLE 7: PIN 1. BASE 2. Emitter 3. Collector	STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE
				STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

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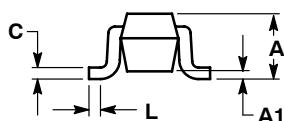
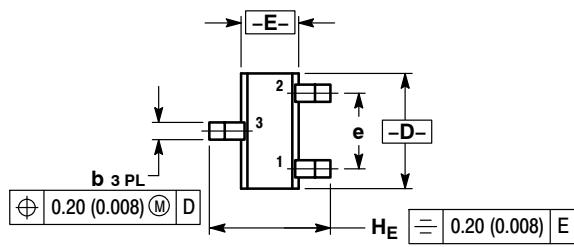
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 4:1



STYLE 1:
PIN 1. BASE
2. Emitter
3. Collector

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

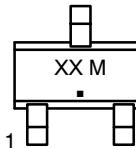
STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00	BSC		0.04	BSC	
L	0.10	0.15	0.20	0.004	0.006	0.008
H_E	1.50	1.60	1.70	0.060	0.063	0.067

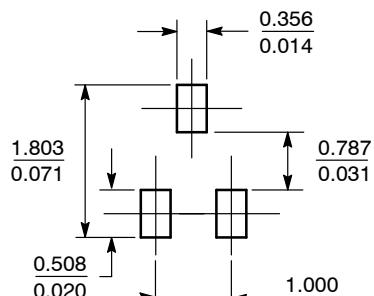
GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

SOLDERING FOOTPRINT*



SCALE 10:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

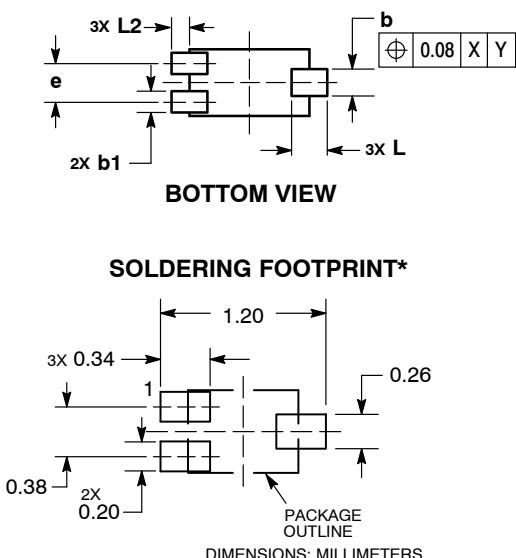
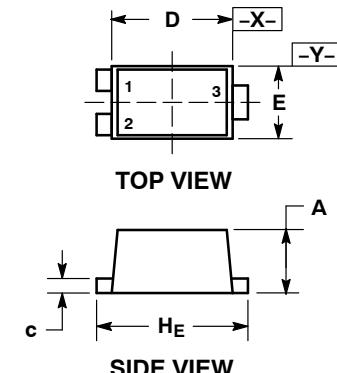
ON Semiconductor®



SOT-1123
CASE 524AA
ISSUE C

DATE 29 NOV 2011

SCALE 8:1



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1: PIN 1. BASE 2. Emitter 3. Collector	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
---	--	--	--	--

NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS		
DIM	MIN	MAX
A	0.34	0.40
b	0.15	0.28
b1	0.10	0.20
c	0.07	0.17
D	0.75	0.85
E	0.55	0.65
e	0.35	0.40
H_E	0.95	1.05
L	0.185 REF	
L2	0.05	0.15

GENERIC MARKING DIAGRAM*



X = Specific Device Code
M = Date Code

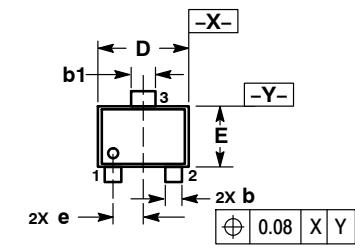
*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "■", may or may not be present.

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DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0.6X0.37, 0.35P	PAGE 1 OF 1

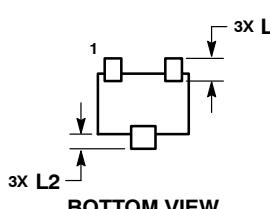
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SCALE 4:1



TOP VIEW



BOTTOM VIEW

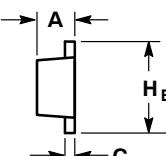
STYLE 1:
PIN 1. BASE
2. Emitter
3. Collector

STYLE 2:
PIN 1. ANODE
2. NC
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

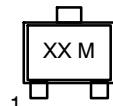


SIDE VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

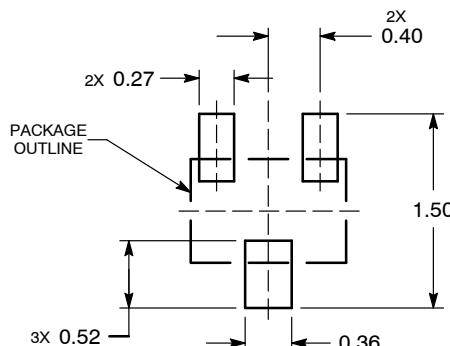
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H_E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SOT-723	PAGE 1 OF 1

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